

UTG50N120FQ-G2 Prelim

Preliminary Ins

Insulated Gate Bipolar Transistor

1200V TRENCH GATE FIELD-STOP IGBT

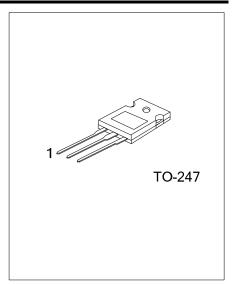
DESCRIPTION

The UTC **UTG50N120FQ-G2** is an Trench Field-Stop Insulated Gate Bipolar Transistor. it uses UTC's advanced technology to provide customers with high switching speed, low saturation voltage and low switching loss, etc.

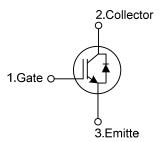
The UTC **UTG50N120FQ-G2** is suitable for the resonant or soft switching applications.

FEATURES

- * High switching speed
- * High avalanche ruggedness
- * Low saturation voltage: V_{CE(SAT).Typ}.= 1.77V @ I_C=50A, V_{GE}=15V (T_C =25°C)



SYMBOL

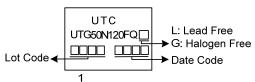


ORDERING INFORMATION

Ordering Number		Package	Pin Assignment		ient	De elsia a	
Lead Free	ree Halogen Free		1	2	3	Packing	
UTG50N120FQL-T47-T	UTG50N120FQG-T47-T	TO-247	G	С	Е	Tube	
Note: Pin Assignment: G: Gate C: Collector E: Emitter							

UTG50N120FQG-T47-T	(1) T: Tube
(2)Package Type	(2) T47: TO-247
(3)Green Package	(3) G: Halogen Free and Lead Free, L: Lead Free

MARKING



PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage		V _{CES}	1200	V
Gate-Emitter Voltage		V _{GES}	±20	V
Transient Gate-emitter voltage (<i>t</i> p < 5 ms)			±25	V
Continuous Collector Current	T _C =25°C		100	А
Continuous Collector Current	T _c =100°C	- Ic	50	А
Collector Current Pulsed (Note 1)		I _{CM}	200	А
Diode Forward Current	T _C =25°C		60	А
Diode Forward Current	T _C =100°C	I _F	30	А
Short Circuit Withstand Time		tsc		
V _{GE} = 15V, V _{CC} ≤ 200V				μs
Allowed number of short circuits < 1000			10	
Time between short circuits: ≥1.0s				
<i>T</i> _{VJ} = 25°C				
Power Dissipation (T _C =25°C)		PD	285	W
Operating Junction Temperature		TJ	-40 ~ +175	°C
Storage Temperature Range		T _{STG}	-55 ~ +175	°C

■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

 Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied. Absolute maximum ratings are those values beyond which the device could be permanently damaged.
2. Pulse width limited by maximum junction temperature.

THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Case	θις	0.44	°C/W



	ELECTRICAL	CHARACTERISTICS	(Tc=25°C, unless otherwise specified)
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PARAMETER	SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT		
Off Characteristics								
Collector-Emitter Breakdown Voltage	BV _{CES}		1200			V		
Collector Cut-Off Current	ICES	V _{CE} =1200V, V _{GE} =0V			250	μA		
G-E Leakage Current	I _{GES}	$V_{CE}=0V, V_{GE}=\pm 20V$			±250	nA		
On Characteristics								
Gate to Emitter Threshold Voltage	V _{GE(TH)}	I _C =250μA, V _{CE} =V _{GE}	4.5		6.5	V		
Collector to Emitter Saturation Voltage	V _{CE(SAT)}	I _C =50A, V _{GE} =15V T _C =25°C T _C =125°C		1.77 2.1	2.3	V V		
Dynamic Characteristics		.6 .20 0			1			
Input Capacitance	CIES		1	2600		pF		
Output Capacitance	COES	V _{CE} =25V, V _{GE} =0V, f=1MHz		108		pF		
Reverse Transfer Capacitance	C _{RES}			71		pF		
Switching Characteristics								
Total Gate Charge	Q _G			198		nC		
Gate-Emitter Charge	Q _{GE}	V _{CE} =600V, I _C =50A, V _{GE} =15V		19.7		nC		
Gate-Collector Charge	Q _{GC}			120.4		nC		
Turn-On Delay Time	t _{DON)}			18.4		ns		
Rise Time	t _R			34.9		ns		
Turn-Off Delay Time	t _{DOFF})	V _{CC} =600V, I _C =50A, R _G =5Ω,		261		ns		
Fall Time	t⊨	V _{GE} =0~15V, L=500µH		216.7		ns		
Turn-On Switching Loss	Eon			3.749		mJ		
Turn-Off Switching Loss	EOFF]		4.64		mJ		
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS								
Forward Voltage Drop	VF	I _F =50A			3.5	V		
Reverse Recovery Time	trr		,	61.2		ns		
Reverse Recovery Charge	Qrr	−I⊧=50A, dI/dt=100A/μS, V _{CC} =400V		1480		nC		
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